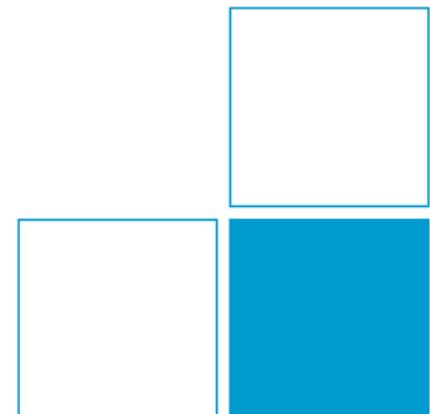


Contamination and Degradation Testing

Alexander Gottwald, UV and VUV radiometry working group

Frank Scholze, EUV radiometry working group



Some Terms

- **Ageing :**

With time or after use it is different than before
(usually: different = worse)

- **Contamination:**

Initially it was clean, but now it's dirty
(removable ! (?))

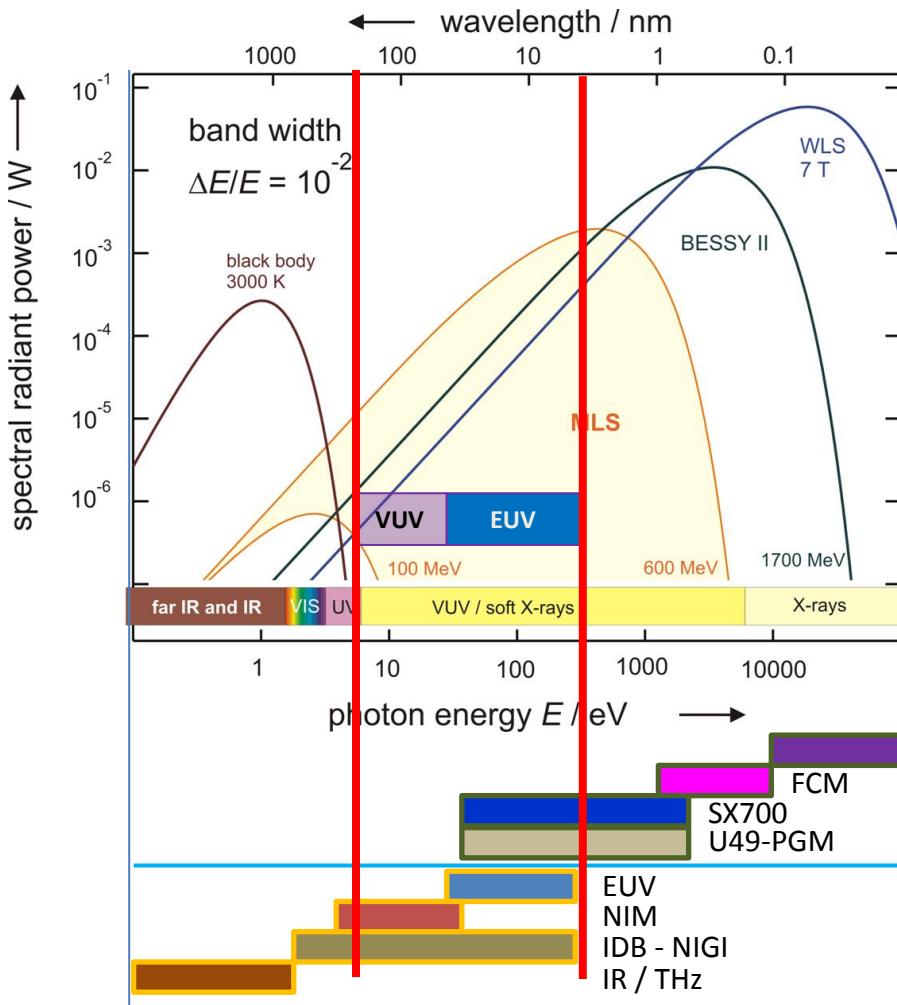
- **Degradation:**

After usage it is damaged now
(can not be recovered)

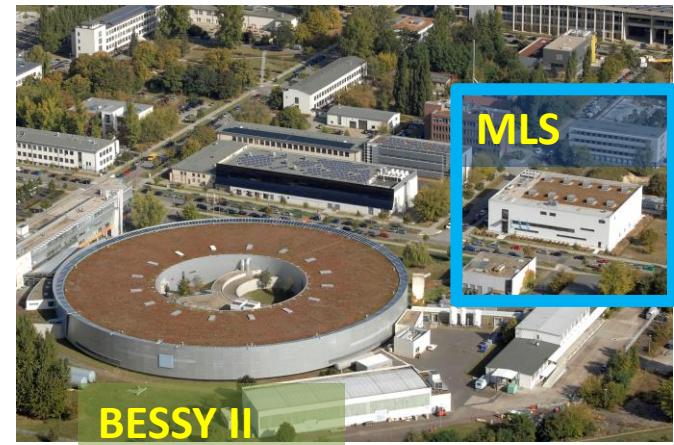
Outline

- Dirt =: D
- Dirt and Radiation =: D+R
 - optical surfaces
 - photodetectors
- $(D + R) - D = R$??
- Prospects

Synchrotron radiation available at PTB



Berlin-Adlershof



PTB monochromator beamlines:

WLS-DCM

BESSY

HZB
Helmholtz
Zentrum Berlin

MLS

PTB

What you (usually) want from PTB

Calibration & characterisation of

optical components:

- filters

spectral transmission

- mirrors

spectral reflectance

- gratings

diffraction efficiency

detectors:

- photodiodes

- photoemissive/
photocathodes

- photoconductive
■ imagers CCD, APS

spectral responsivity

spectrometers:

- dispersive type (grating)

- filter radiometer type

- ...

spectral responsivity

irradiance sensitivity

...

What you (usually) get from PTB

- **measurement value + uncertainty**
- uncertainty budget is for measurement conditions at PTB calibration
- does not include different measurement conditions and ageing

“true” value ?

vs.

“real value” ?

- ideal conditions
- determination of material parameters
- comparison to theoretical models

- real conditions
- determination of performance parameters
- comparison to other measurements

difficult to realise (but PTB attempts)

practical use??

Conditions during calibration the same as in your apparatus ?

How big is the discrepancy ?

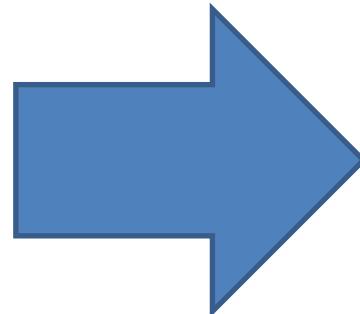


our experience: typically < 5 % without (!) aging

How to approach the “true” value

Sample with initial adsorbates from:

- processing ■ transport ■ pumpdown

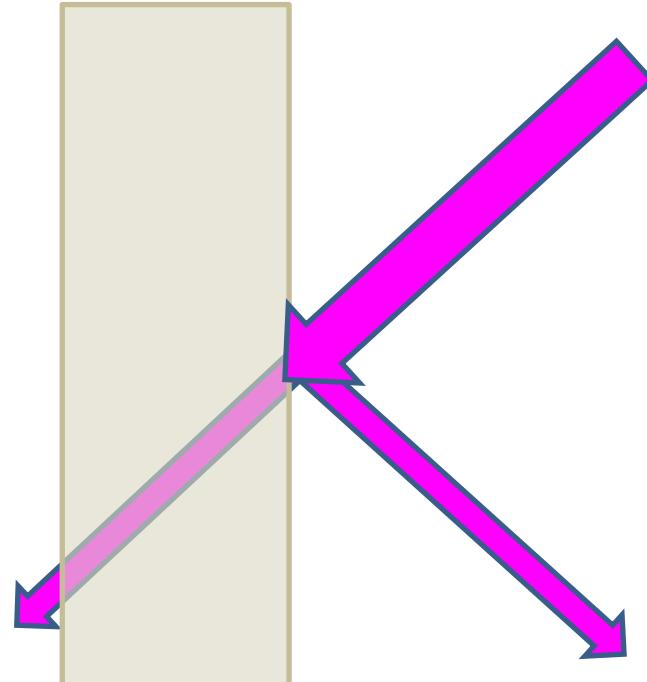


surface cleaning:

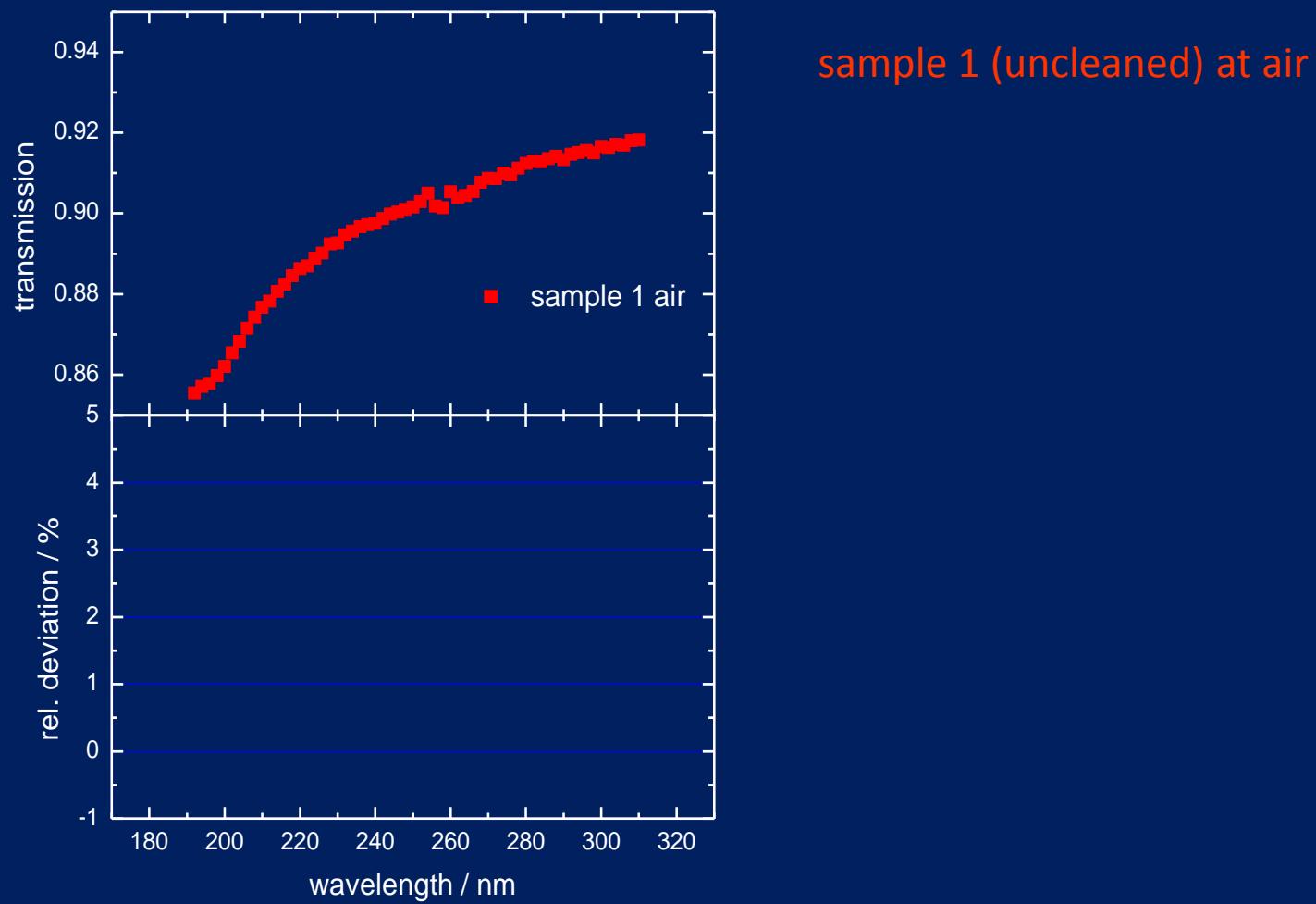
- in-air UV-ozone cleaning
- in-vacuum heating / bakeout
- in-vacuum plasma cleaning (RF, DC; Ar, O₂, H₂)

Cleaned sample for measurement

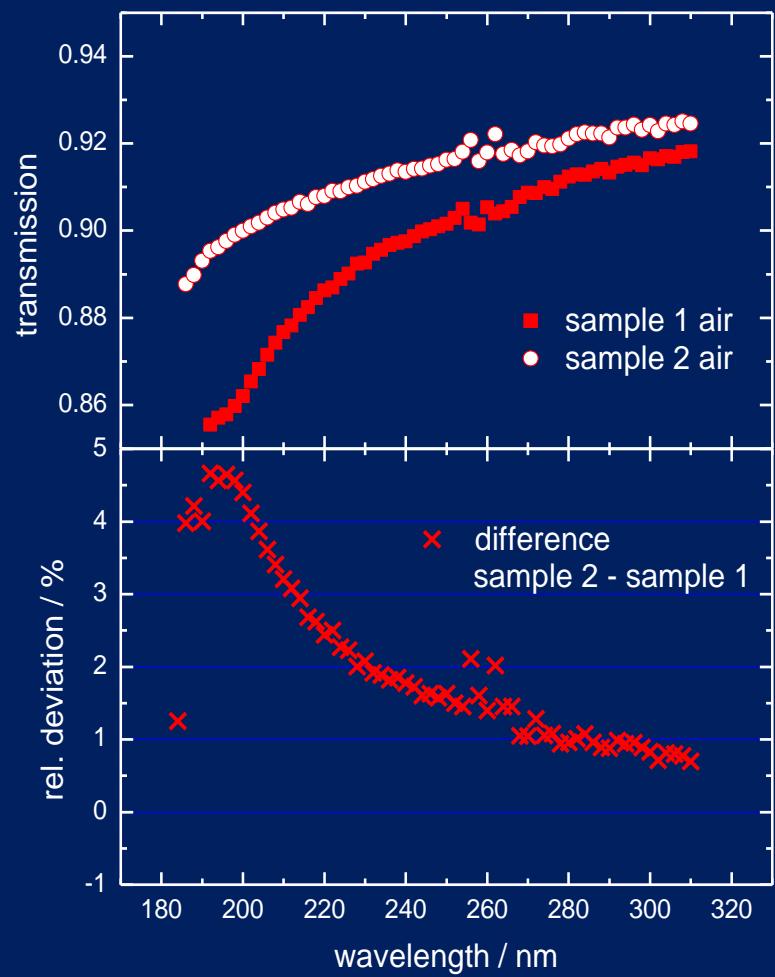
- reflectance ■ transmission ■ efficiency



“Simple” example: quartz transmission standard



“Simple” example: quartz transmission standard

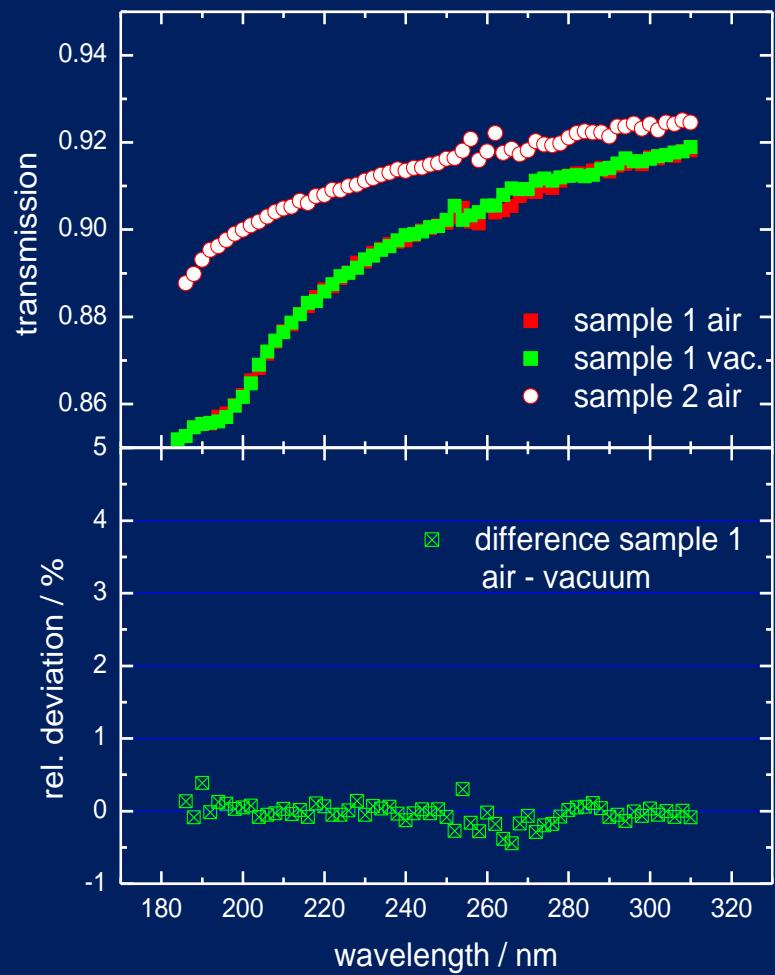


sample 1 (uncleaned) at air

sample 2 (UV cleaned) at air

difference cleaned/uncleaned:
up to 4 % !

“Simple” example: quartz transmission standard



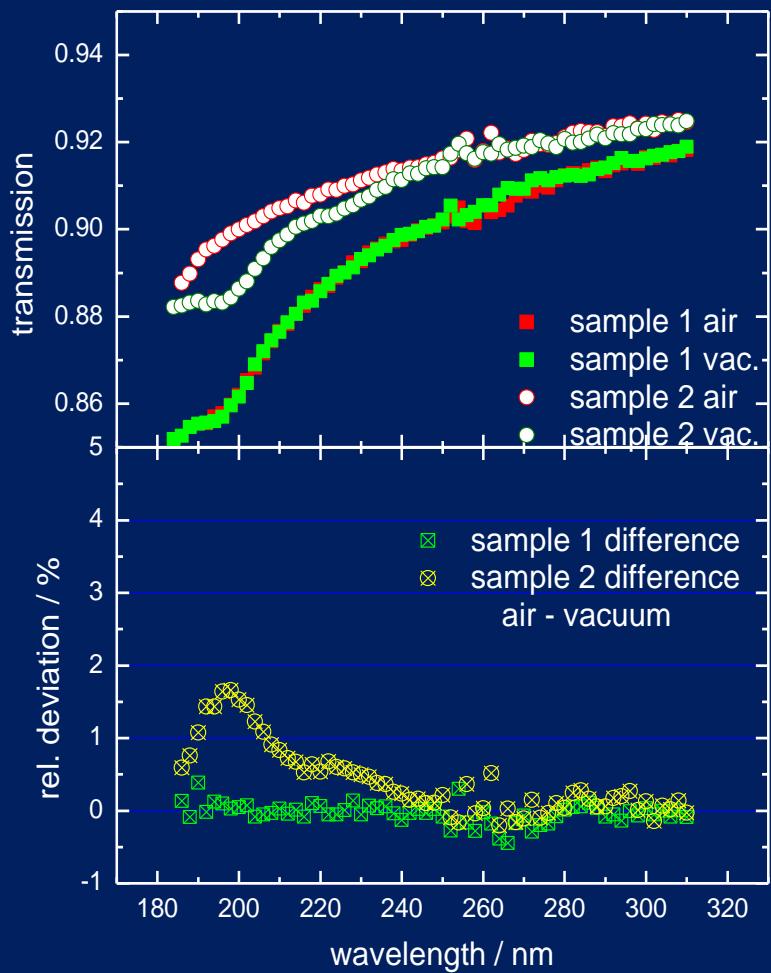
sample 1 (uncleaned) at air

sample 1 (uncleaned) at vacuum

sample 2 (UV cleaned) at air

uncleaned sample (1):
NO difference air - vacuum

“Simple” example: quartz transmission standard



sample 1 (uncleaned) at air

sample 1 (uncleaned) at vacuum

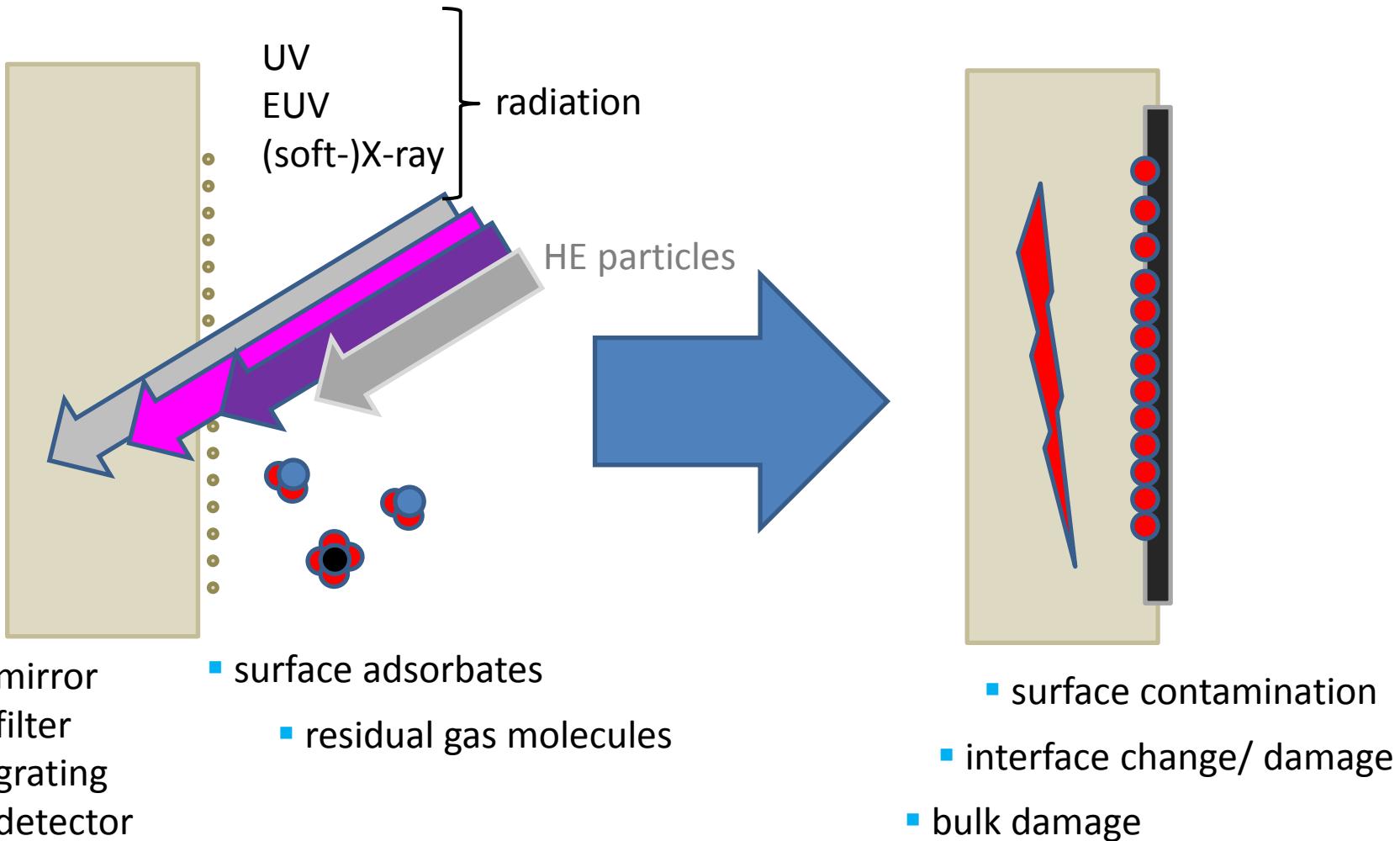
sample 2 (UV cleaned) at air

sample 2 (UV cleaned) at vacuum

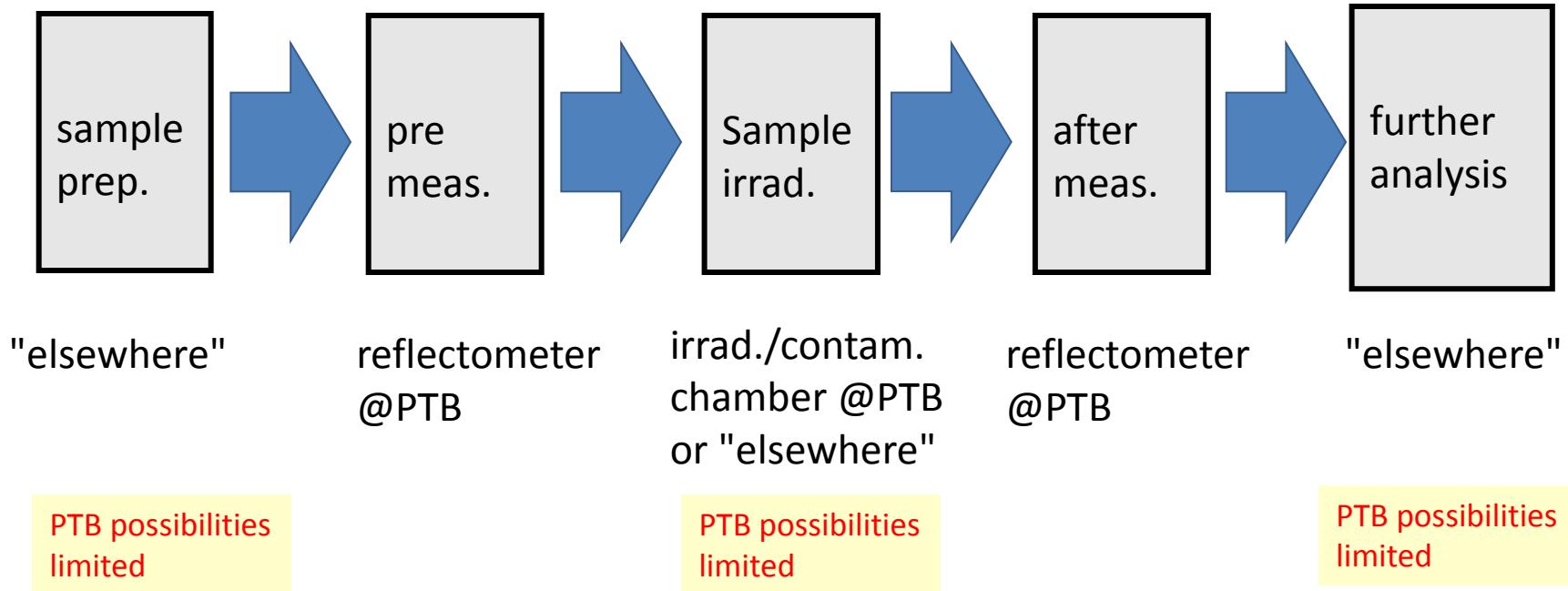
uncleaned sample (1):
NO difference air - vacuum

UV cleaned sample (2):
up to 2 % difference!

Change by irradiation



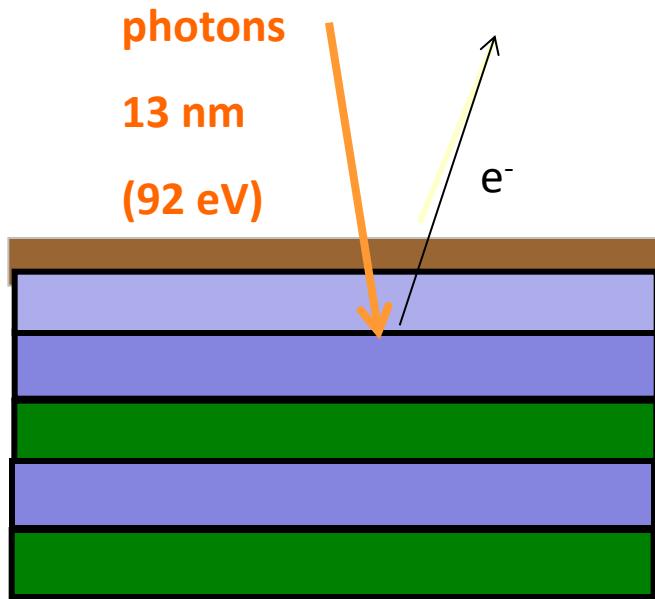
Typical measurement sequence



Problems:

- ambient air exposure during transport
- inadequate conditions e.g. during irradiation

The EUVL experience (from 2001 on)



Oxidation

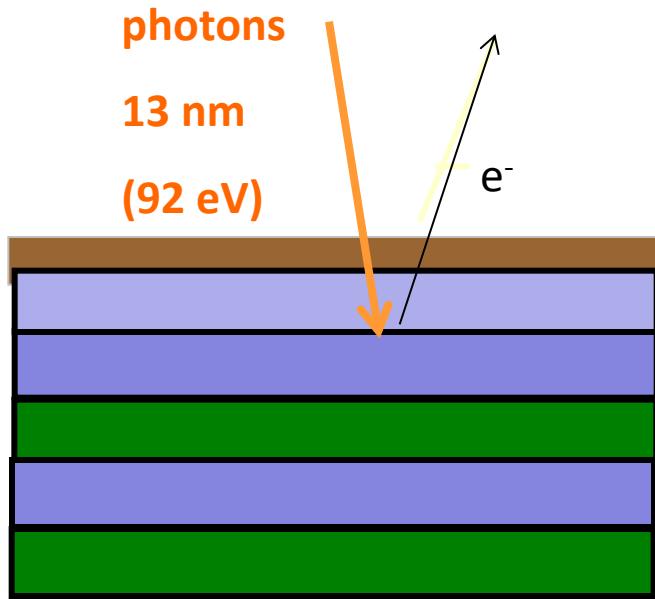
... on Mo/Si multilayers

contamination layer: C_xH_x, H₂O,...
passivation layer, cap layer, oxide

- Si + H₂O + **slow electron** = oxidation enhancement
 - **Oxidation is irreversible**
 - Mitigation of oxidation in the presence of EtOH
 - Formation of **self-terminating C-layer**
- ⇒ **Initial capping with C-layer prevents oxidation**
- but: hydrocarbons will let the C-layer grow**

Koster et al., Microelectric Engineering 61-62 (2002), 65-76

The EUVL experience (from 2001 on)



Carbon growth (similar on metal surfaces)

contamination layer
passivation layer, oxide

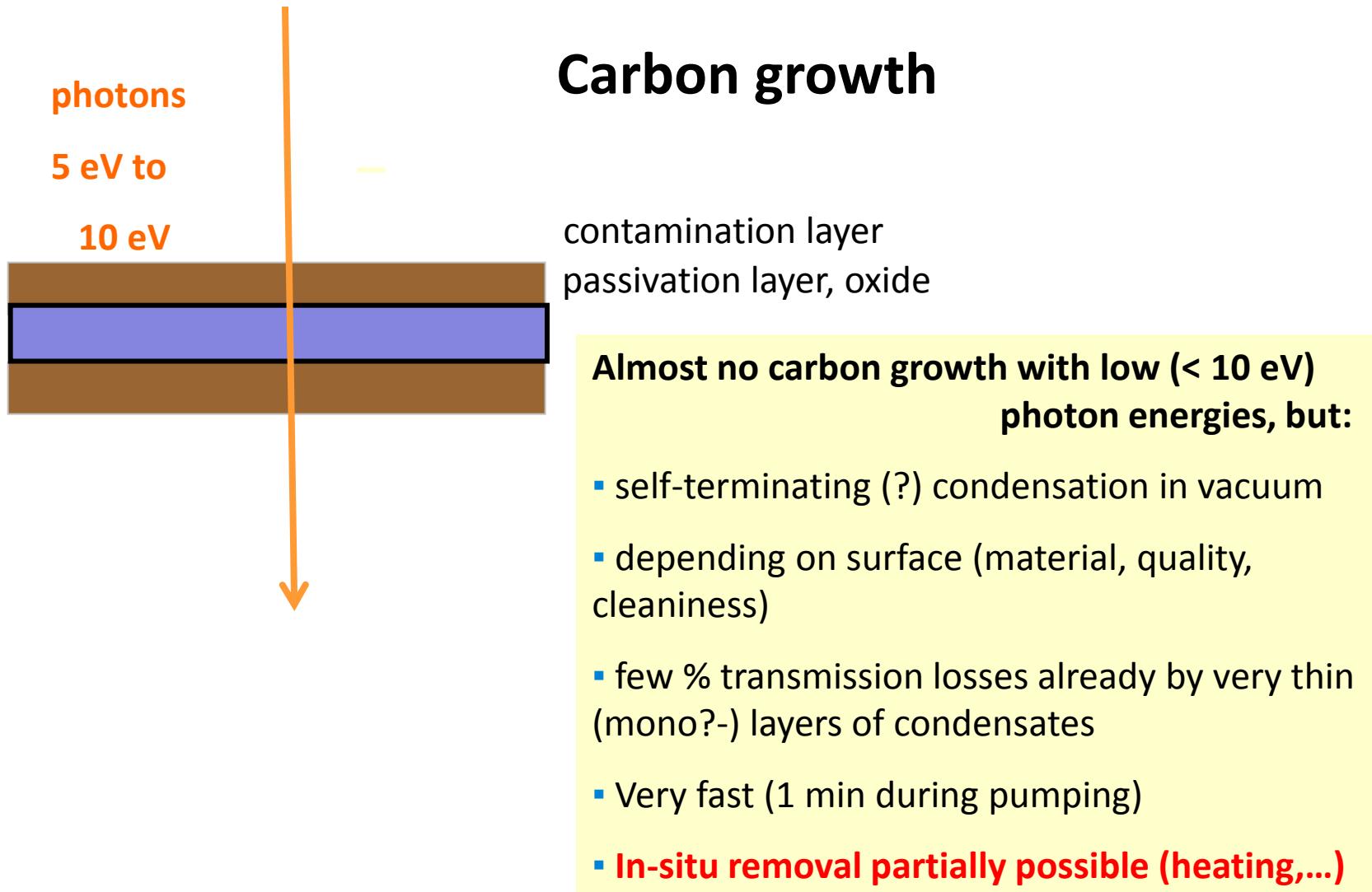
carbon layer growth depends on

- absolute amount of hydrocarbons
- type (mass number) of hydrocarbons
- energy of photons
- number of photons (irradiation)
- (surface material)

can be removed and initial values can be restored

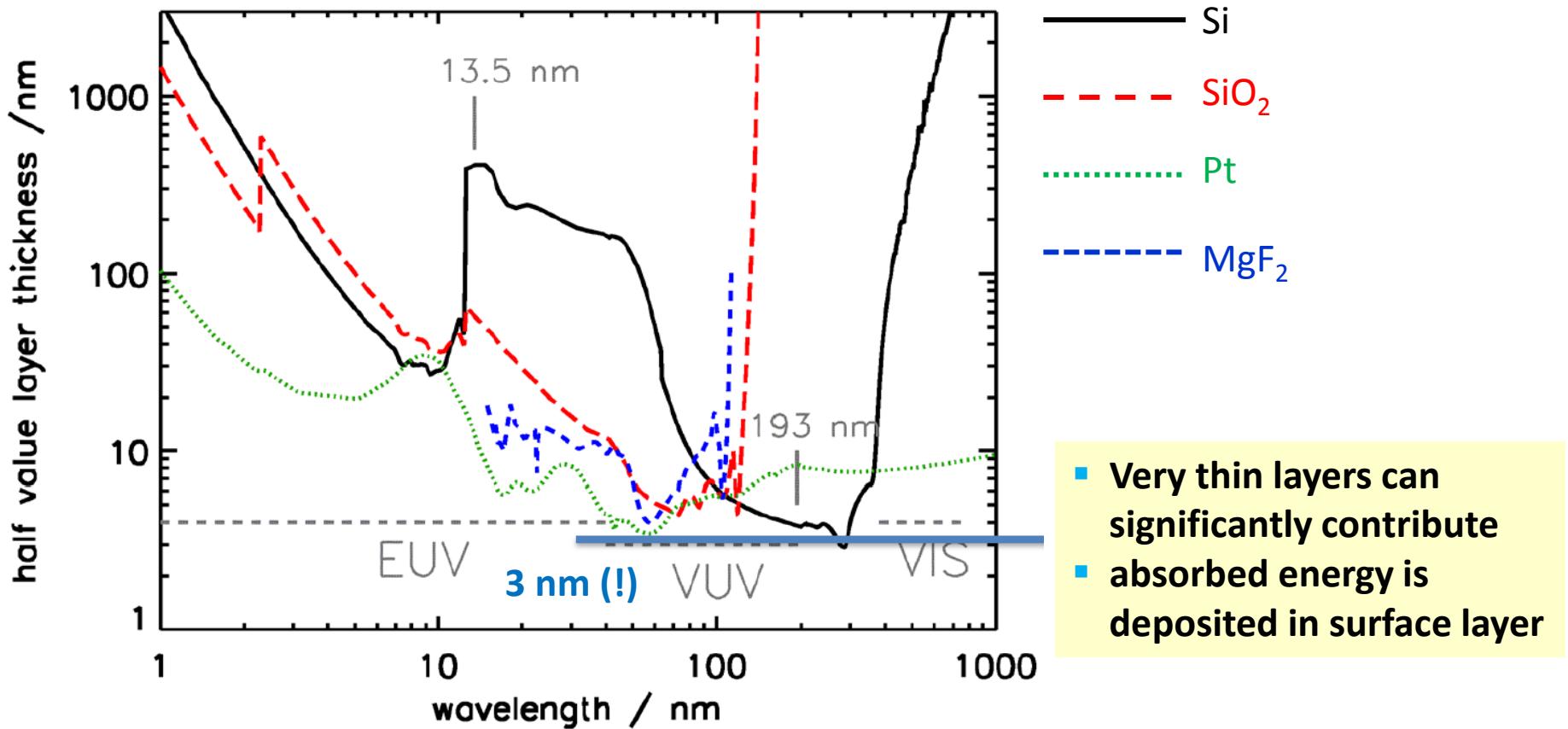
Koster et al., Microelectric Engineering 61-62 (2002), 65-76

Further experiences (in VUV)

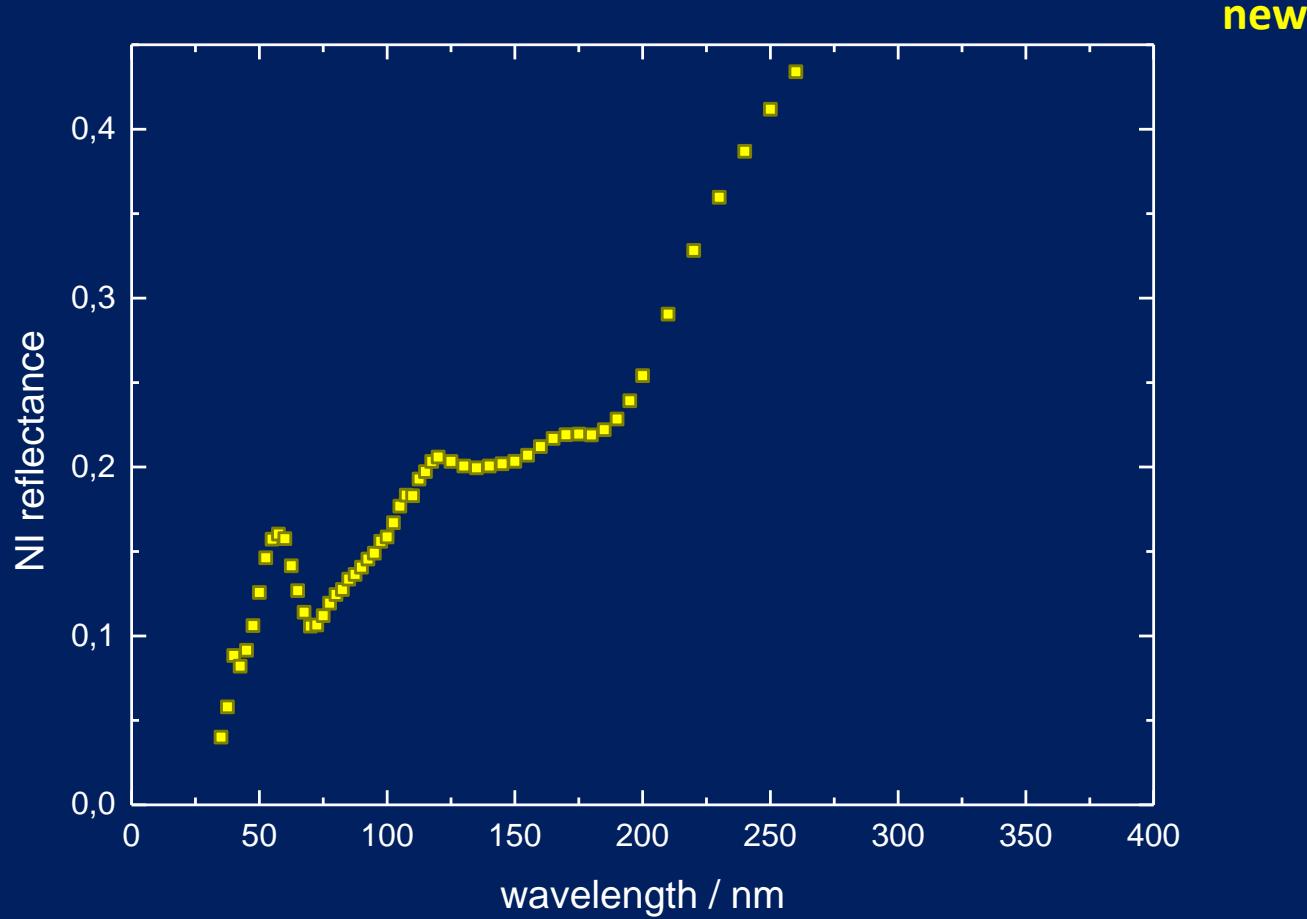


Why wavelengths matters...

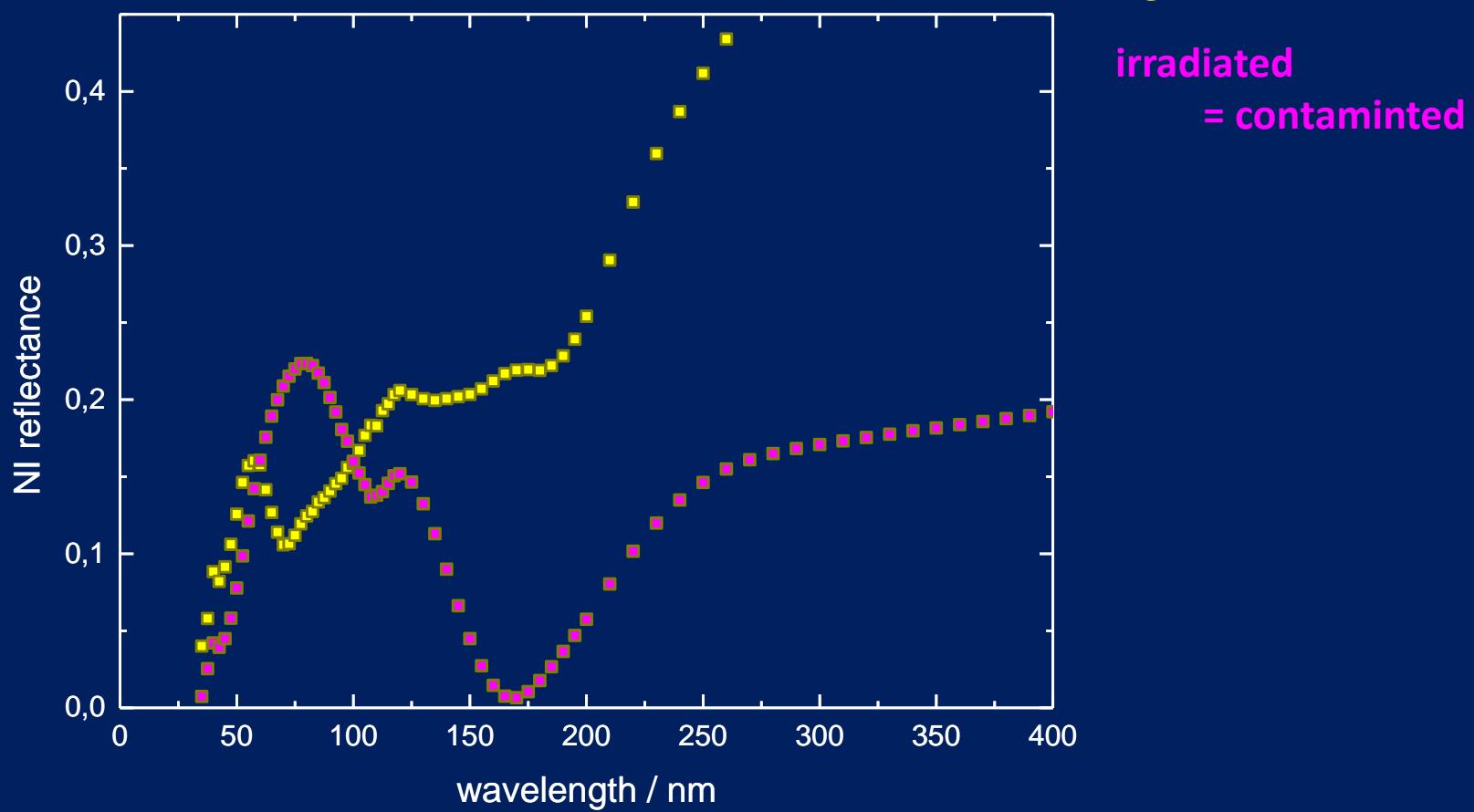
- half-value layer thickness of representative materials



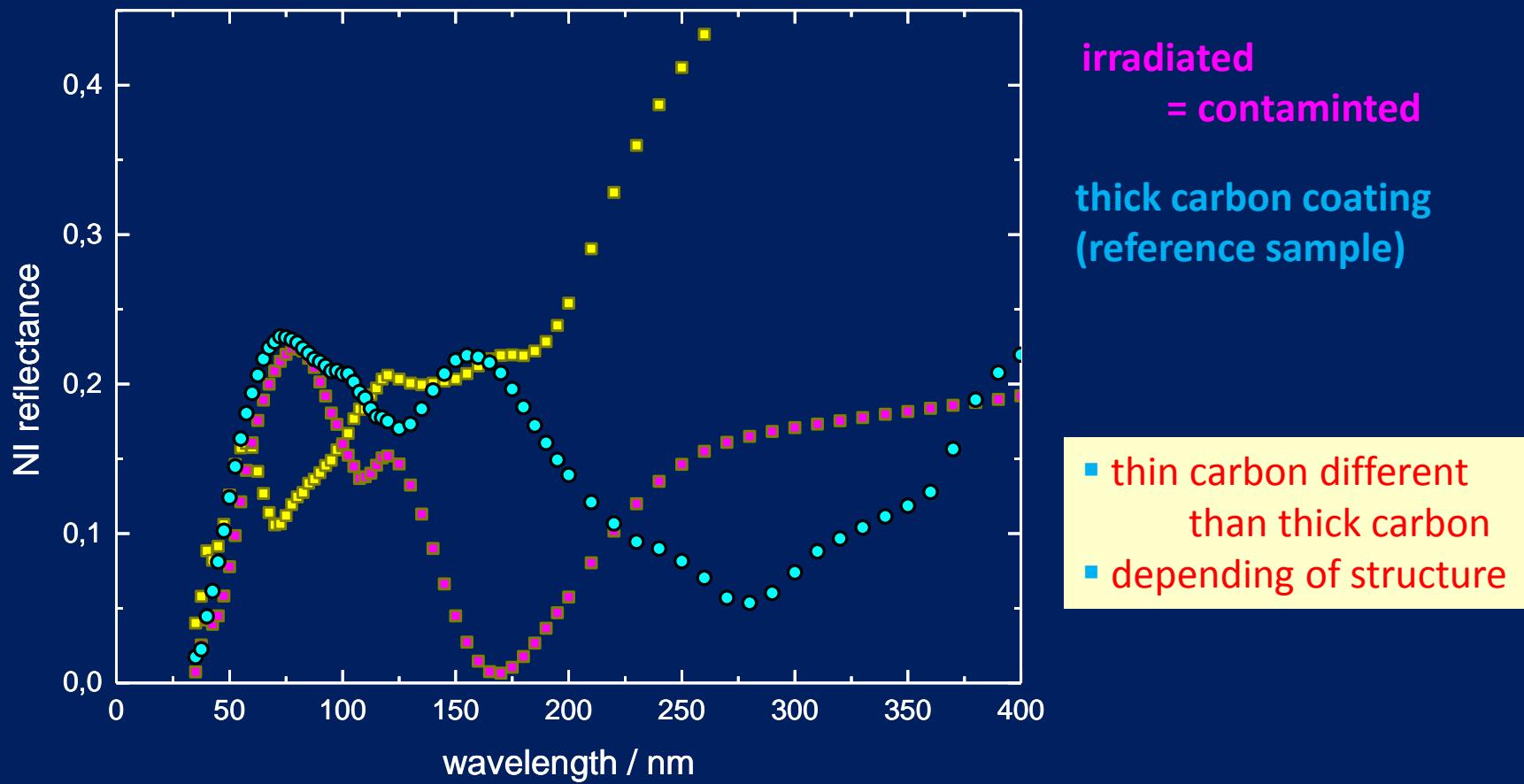
Example: Pt mirror



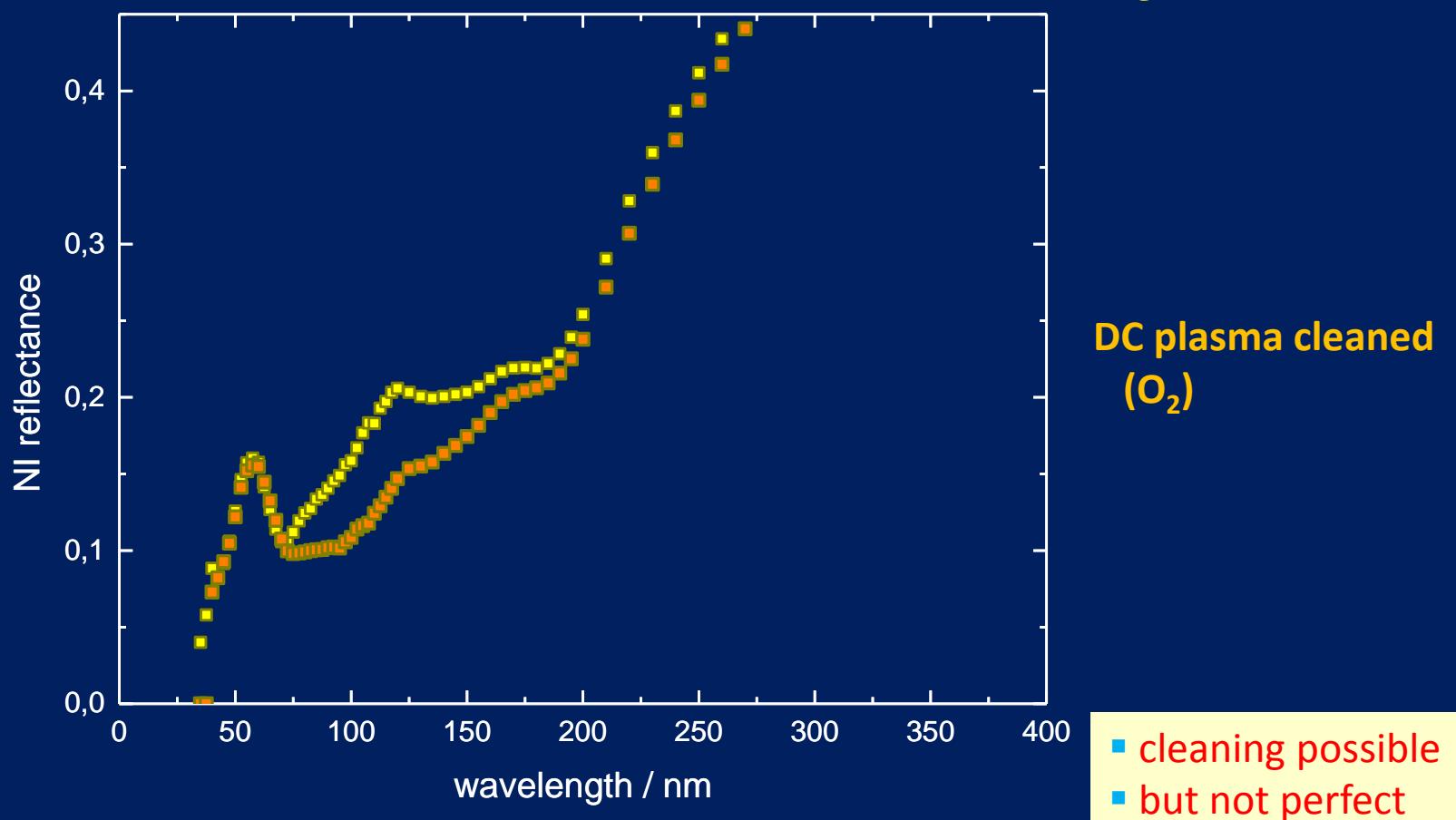
Example: Pt mirror



Example: Pt mirror

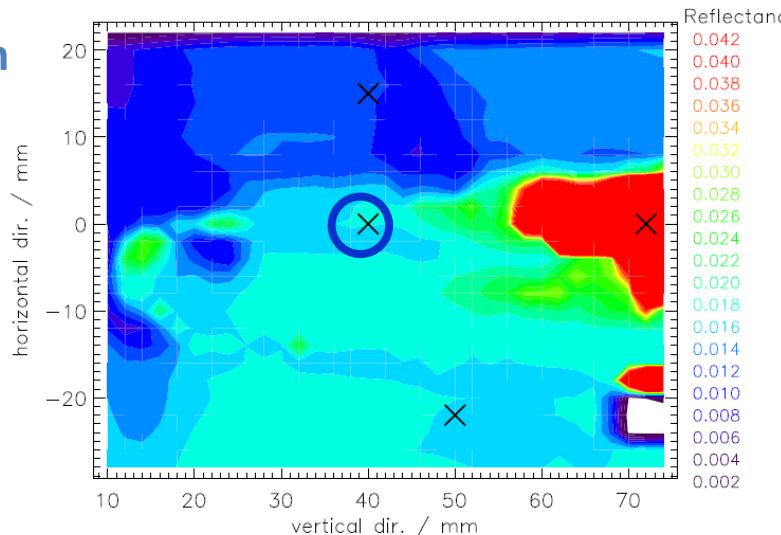


Example: Pt mirror

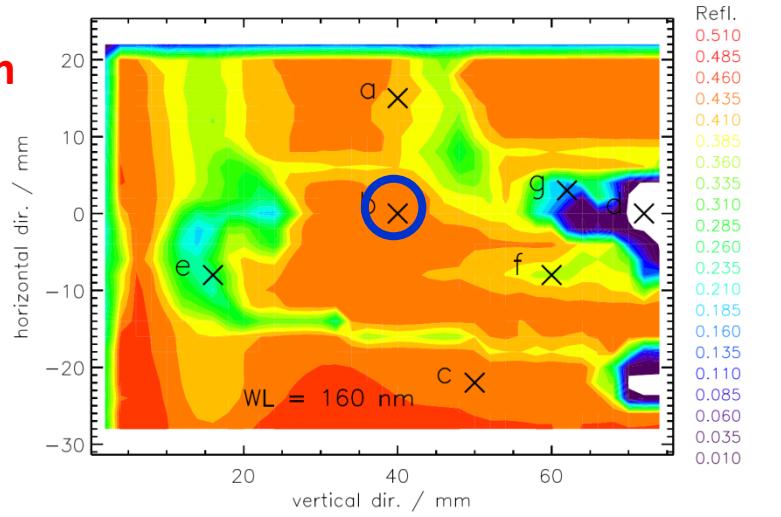


Example: C-coated Si Mirror

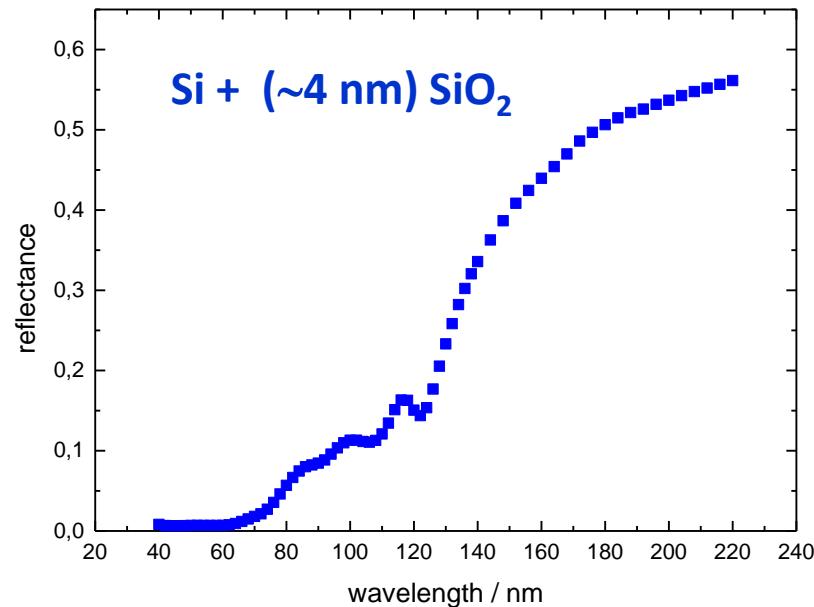
70 nm



160 nm

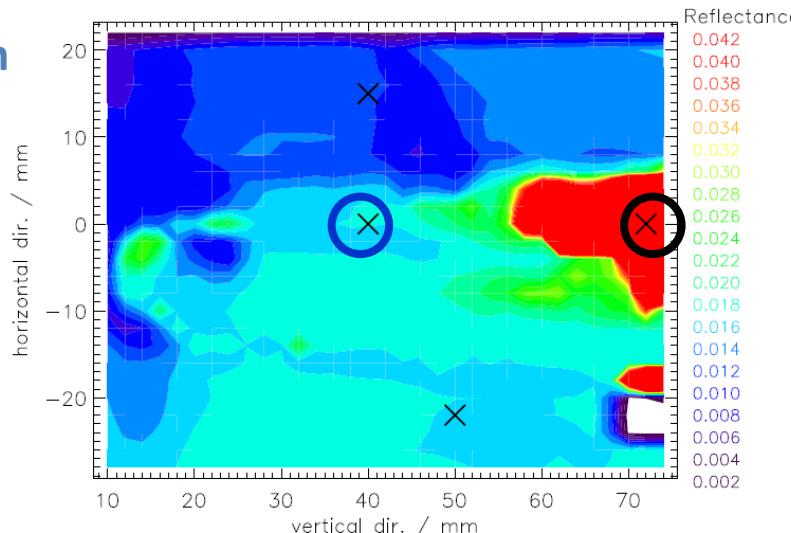


- exposed to GW EUV pulses (DESY FEL)
- reconstruction of C configuration observed ("needles")
- massive plasma cleaning for re-coating
- non-uniform residuals remaining
- multiple analysis performed,
here: VUV reflectometry

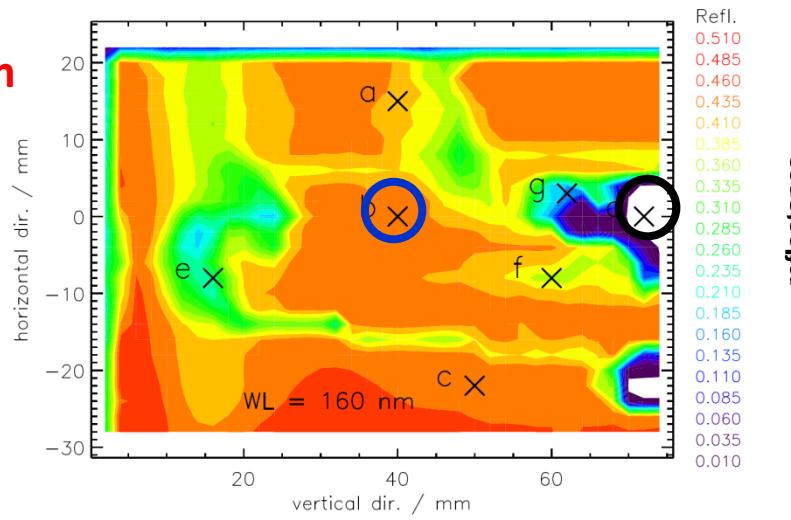


Example: C-coated Si Mirror

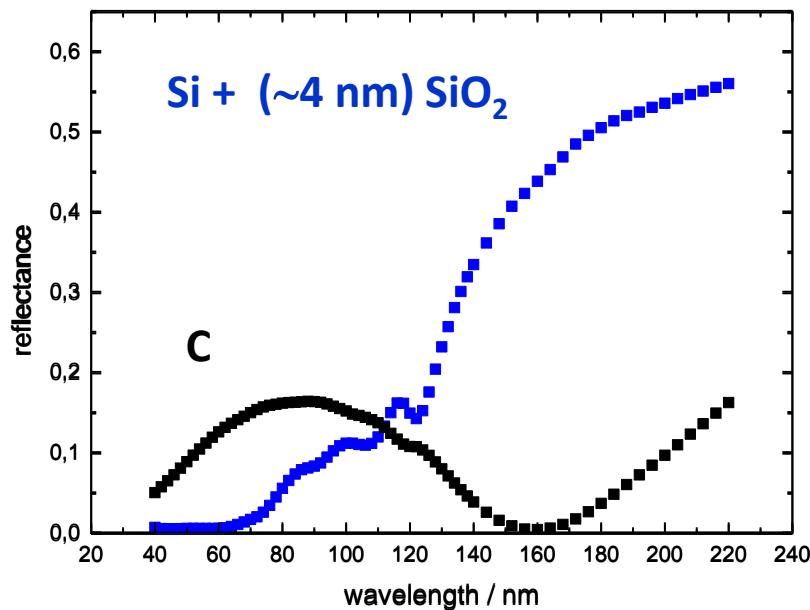
70 nm



160 nm

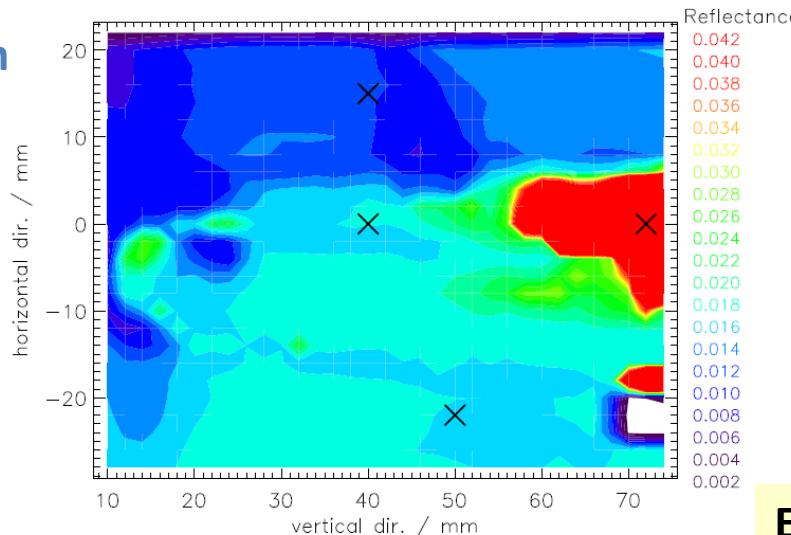


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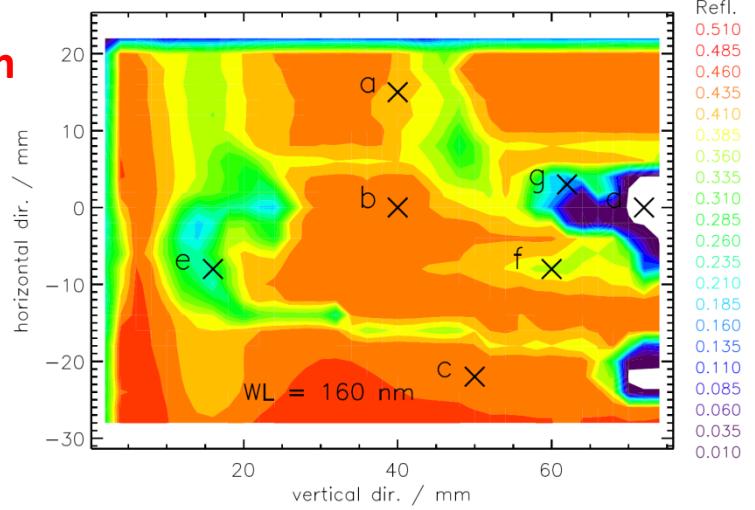


Example: C-coated Si Mirror

70 nm



160 nm



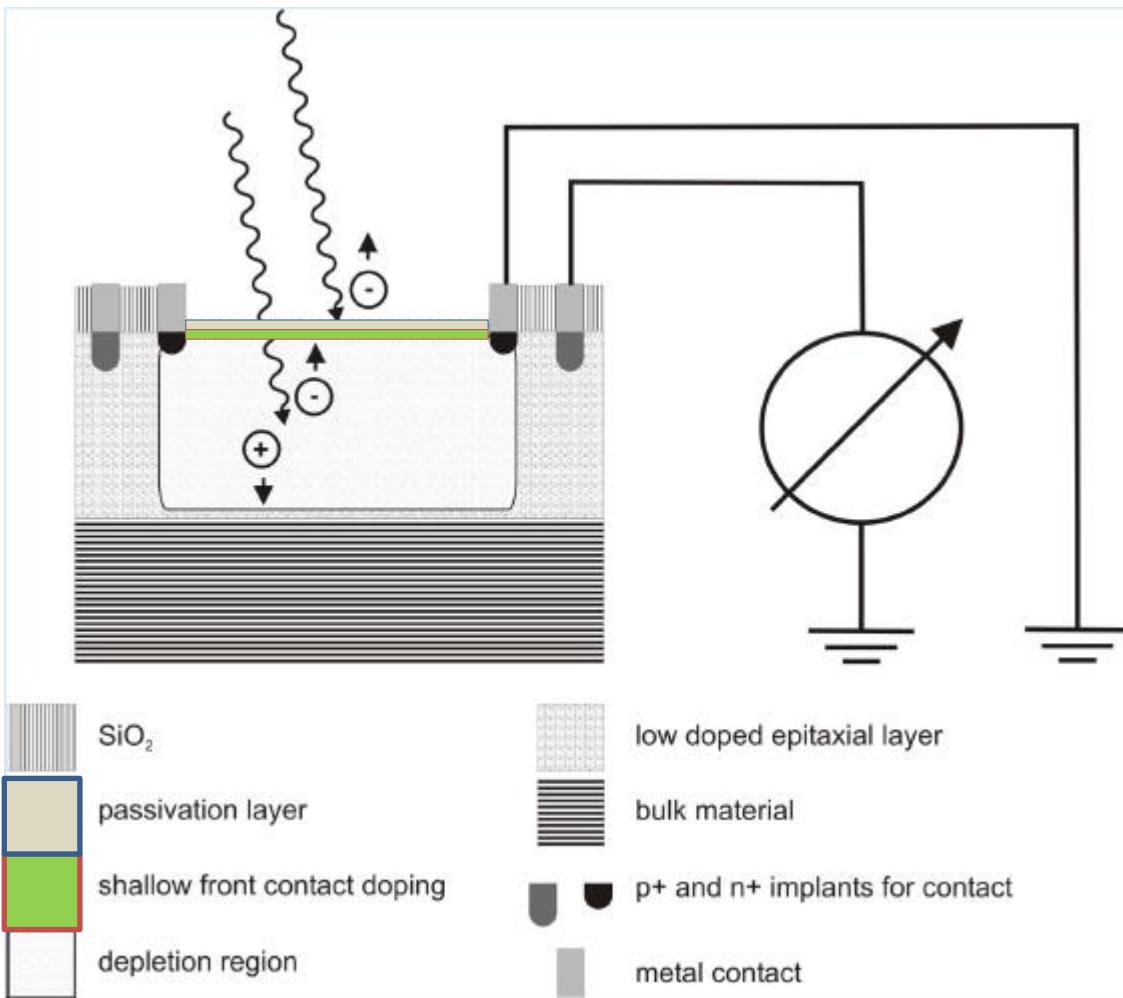
- exposed to GW EUV pulses (DESY FEL)
- reconstruction of C configuration observed ("needles")
- massive plasma cleaning for re-coating
- non-uniform residuals remaining
- multiple analysis performed,
here: VUV reflectometry

EUV/VUV reflectometry:

- modeling (layer material and thickness) is possible if opt. constants are known
- surface sensitive (few nm)
- no buried layer analysis
- no speciation or chemical structure analysis

Further analysis required to investigate specific processes !

Detectors



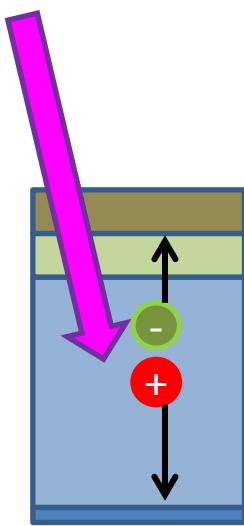
„typical“ Si photodiode

- surface contamination
- interface change/damage
- bulk damage

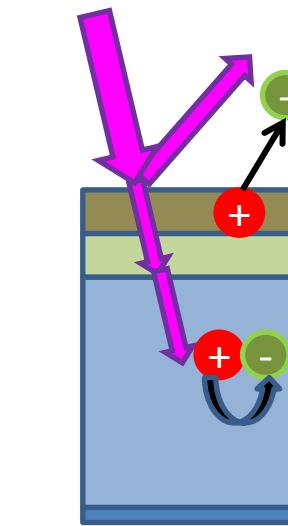
change of spectral responsivity

Primary effects in radiation detection

passivation layer
front contact doping
depletion zone
substrate



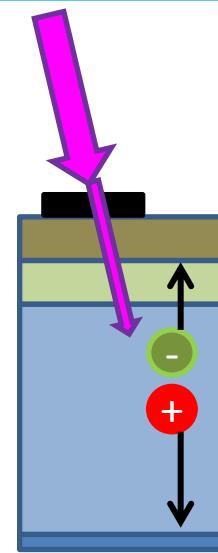
ideal case



loss mechanisms

- Surface reflection
- (photo)electron loss
- dead layer absorption
- recombination

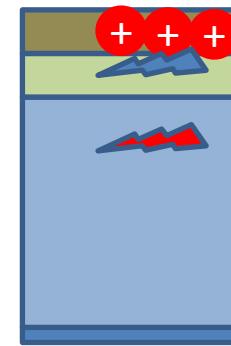
unavoidable



contamination

- additional absorbtion
- local effects !
- photochemistry (carbon growth)

removable

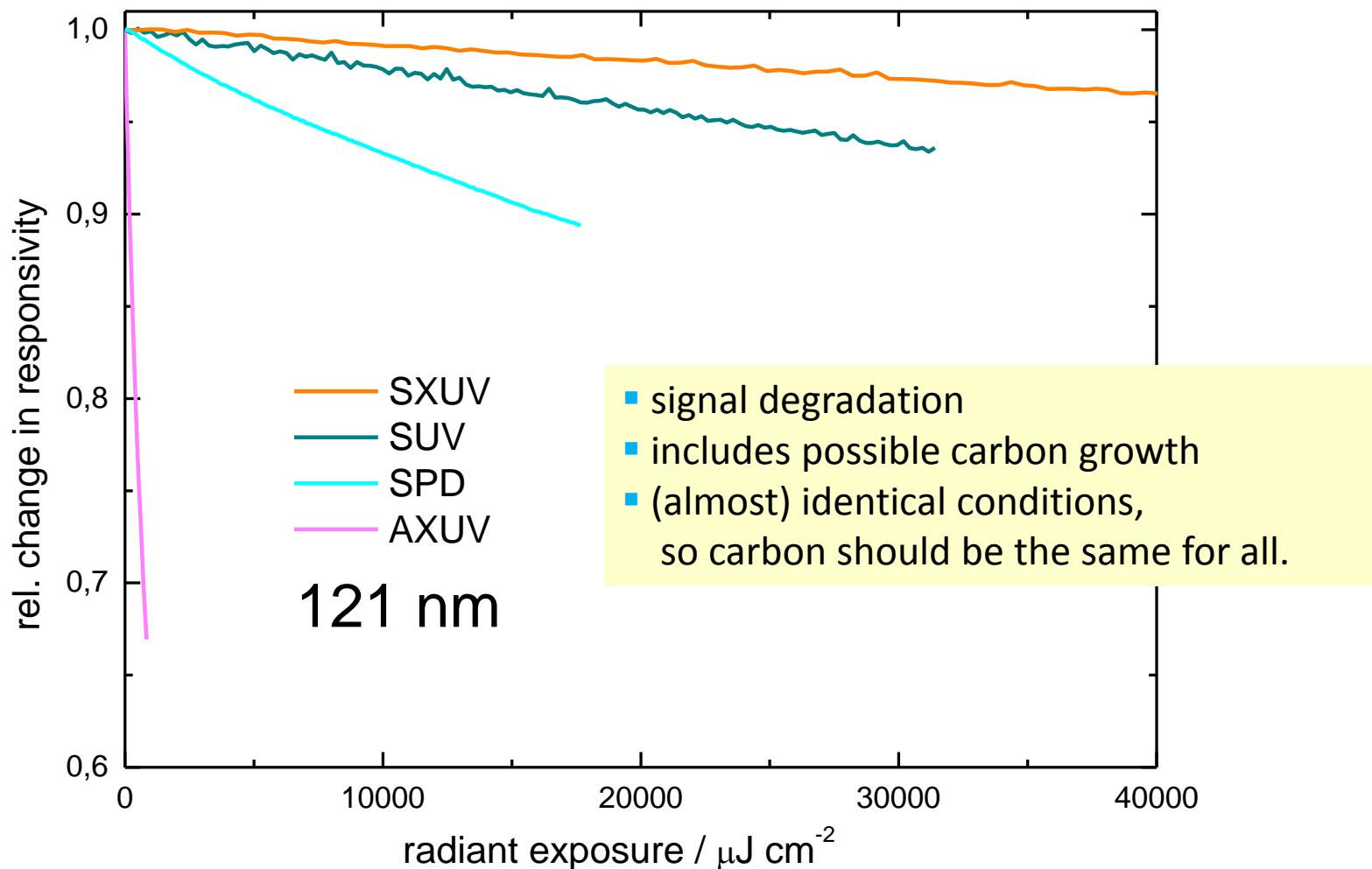


ageing & damage

- surface charge
- interface oxidation
- trap state creation (CCE change)

can be minimized by detector design

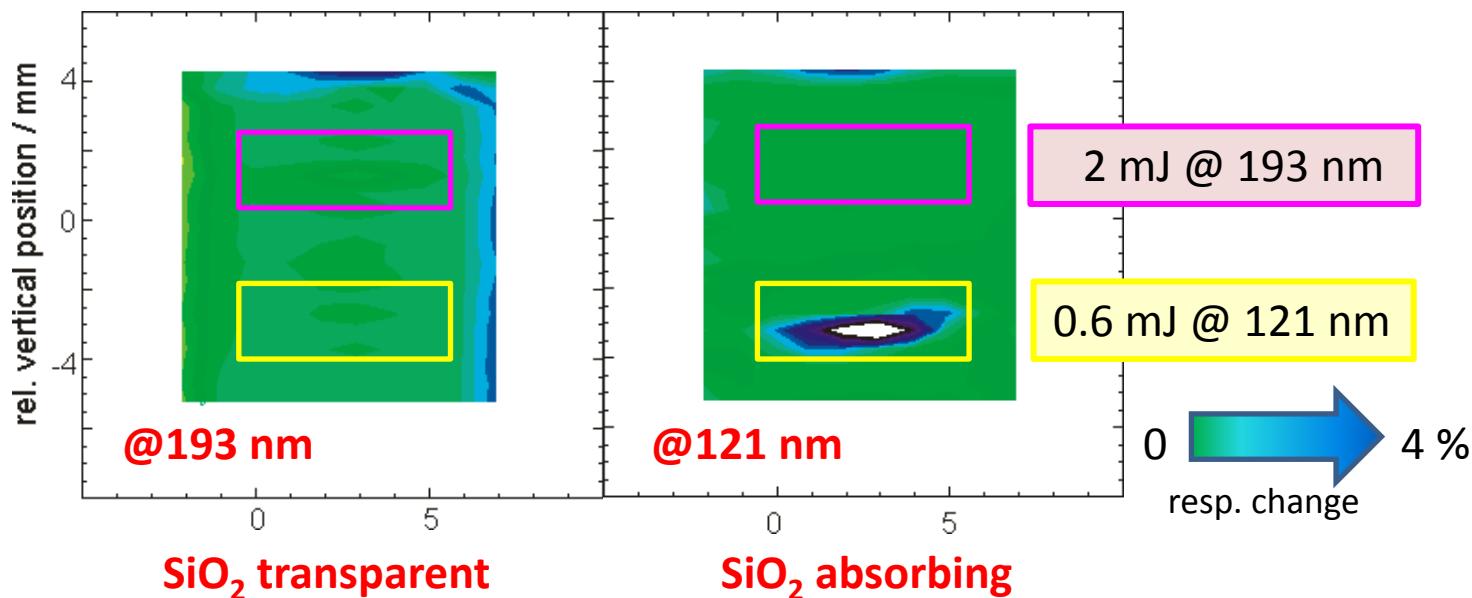
Irradiation Ageing



Example for ageing: Si photodiode

AXUV-100G photodiode 10 mm x 10 mm

Relative spectral responsivity map:

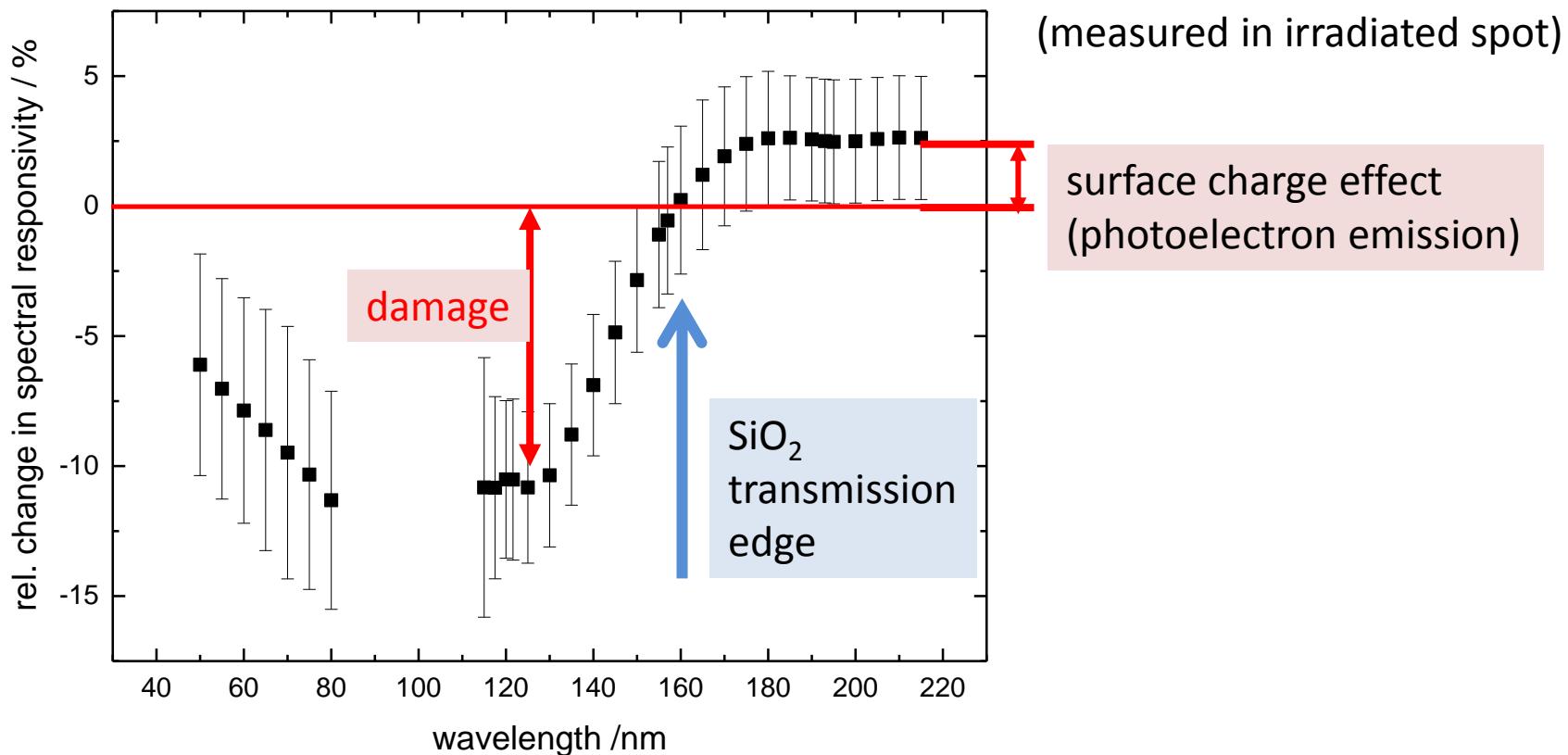


- weak effect of 193 nm irrad.
- massive effect of 121 nm irradiation
- irreversible damage of the SiO₂ passivation layer**
cannot be removed by surface cleaning

Example for ageing: Si photodiode

AXUV-100G photodiode 10 mm x 10 mm

change of spectral responsivity with wavelength after 121 nm irradiation

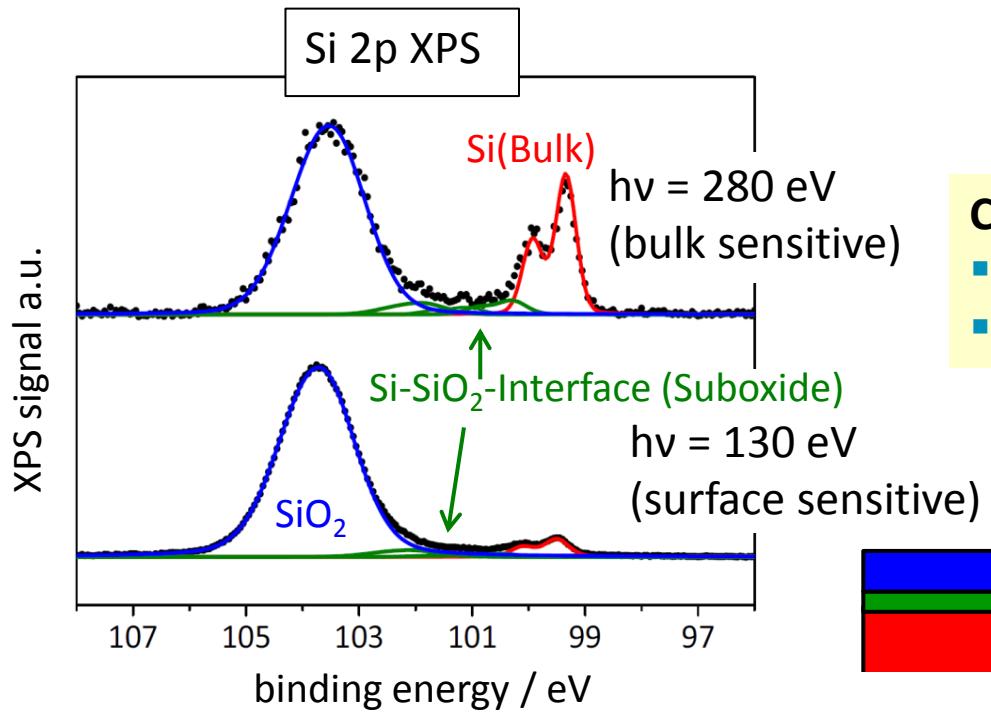


Outlook: Surface analysis to understand processes

Electron spectroscopy (XPS/UPS):
chemical speciation possible
learn about surface processes

Further Methods at PTB
in the (soft-)X-ray range:
spectroscopic ellipsometry,
XRF, XRR, NEXAFS

Example: XPS spectra of different Si oxidation states



Change of probing photon energy:

- Element sensitivity (cross sections)
- Probing depths (mean free path)

E. Darlatt

Conclusions

1. Contamination can lead to deviating calibration results
even at low irradiation levels
2. *In situ* sample cleaning can (at least partially) remove contamination effect,
ex situ sample cleaning might even enhance (later) contamination!
3. Irradiation (UV or shorter wavelength) can result in:
 - carbon growth ■ interlayer change (oxidation, ...) ■ structural (bulk) damage
4. Differentiation between contamination and (other) degradation is not always possible
5. Prediction of effects (and inclusion into the uncertainty budget) is difficult since:
 - environment parameters for contamination are difficult to control
 - processes are still not well understood (\Rightarrow **further research work needed**)
6.
 - avoid ambient air (humidity, hydrocarbons)
 - if it is unavoidable, define reproducible cleaning and measuring procedures



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